RGS80TS65HR

650V 40A Field Stop Trench IGBT

Datasheet

V _{CES}	650V
I _{C (100°C)}	40A
V _{CE(sat) (Typ.)}	1.65V
P_{D}	272W

Outline TO-247N

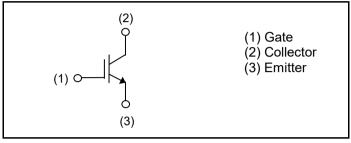
Features

- 1) Low Collector Emitter Saturation Voltage
- 2) Short Circuit Withstand Time 8µs
- 3) Qualified to AEC-Q101
- 4) Pb free Lead Plating; RoHS Compliant

Application

Heater for Automotive

●Inner Circuit



Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	-
Tuna	Tape Width (mm)	-
Type	Basic Ordering Unit (pcs)	450
	Packing Code	C11
	Marking	RGS80TS65

● **Absolute Maximum Ratings** (at T_C = 25°C unless otherwise specified)

	. ,			
Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V _{CES}	650	V
Gate - Emitter Voltage		V_{GES}	±30	V
Collector Current	T _C = 25°C	I _C	73	А
	T _C = 100°C	I _C	40	А
Pulsed Collector Current		I _{CP} *1	120	А
Power Dissipation	T _C = 25°C	P _D	272	W
	T _C = 100°C	P _D	136	W
Operating Junction Temperature		T _j	T _j -40 to +175	
Storage Temperature		T _{stg}	-55 to +175	°C

^{*1} Pulse width limited by T_{imax.}

●Thermal Resistance

Parameter	Symbol	Values			Unit
raiametei	Symbol	Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	1	ı	0.55	°C/W

●IGBT Electrical Characteristics (at T_i = 25°C unless otherwise specified)

Parameter	Cumbal	Conditions	Values			Linit
Parameter	Symbol		Min.	Тур.	Max.	Unit
Collector - Emitter Breakdown Voltage	BV _{CES}	$I_{C} = 10 \mu A, V_{GE} = 0 V$	650	-	-	V
		$V_{CE} = 650V, V_{GE} = 0V,$				
Collector Cut - off Current	I _{CES}	$T_{j} = 25^{\circ}C$ $T_{j} = 175^{\circ}C^{*2}$	-	-	10	μΑ
		Tj = 175°C ^{*2}	ı	ı	5	mA
Gate - Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 30V, V_{CE} = 0V$	-	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{\text{GE(th)}}$	$V_{CE} = 5V, I_{C} = 2.0mA$	5.0	6.0	7.0	V
Collector - Emitter Saturation Voltage		$I_C = 40A, V_{GE} = 15V,$				
	V _{CE(sat)}	T _j = 25°C	-	1.65	2.10	V
		T _j = 175°C	-	2.15	-	V

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Danamatan	0	Conditions		l locit		
Parameter	Symbol		Min.	Тур.	Max.	Unit
Input Capacitance	C _{ies}	V _{CE} = 30V,	-	1240	-	
Output Capacitance	C _{oes}	$V_{GE} = 0V$,	-	103	-	pF
Reverse transfer Capacitance	C_{res}	f = 1MHz	-	16	-	
Total Gate Charge	Q_g	V _{CE} = 300V,	-	48	-	
Gate - Emitter Charge	Q_{ge}	I _C = 40A,	-	12	-	nC
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	19	-	
Turn - on Delay Time	t _{d(on)}		-	37	1	
Rise Time	t _r	$I_C = 40A, V_{CC} = 400V,$ $V_{GE} = 15V, R_G = 10\Omega,$	-	17	-	no
Turn - off Delay Time	$t_{d(off)}$	$T_i = 25^{\circ}C$	-	112	-	ns
Fall Time	t _f	Inductive Load	-	96	-	
Turn - on Switching Loss	E _{on}	*E _{on} include diode reverse recovery	-	1.05	-	mJ
Turn - off Switching Loss	E _{off}	,	-	1.03	1	
Turn - on Delay Time	t _{d(on)}		-	34	-	
Rise Time	t _r	$I_C = 40A, V_{CC} = 400V,$ $V_{GE} = 15V, R_G = 10\Omega,$	-	28	-	ns
Turn - off Delay Time	t _{d(off)}	$T_i = 175^{\circ}C$	-	141	-	
Fall Time	t _f	Inductive Load	-	150	-	
Turn - on Switching Loss	E _{on}	*E _{on} include diode reverse recovery	-	1.43	1	mJ
Turn - off Switching Loss	E_{off}		1	1.47	1	1113
Reverse Bias Safe Operating Area	RBSOA	$I_C = 120A$, $V_{CC} = 520V$, $V_P = 650V$, $V_{GE} = 15V$, $R_G = 50\Omega$, $T_j = 175^{\circ}C$	FULL SQUARE		-	
Short Circuit Withstand Time	t _{sc}	$V_{CC} \le 360V$, $V_{GE} = 15V$, $T_j = 25^{\circ}C$	8	-	-	μs
Short Circuit Withstand Time	t _{sc} *2	$V_{CC} \le 360V$, $V_{GE} = 15V$, $T_j = 150$ °C	6	-	-	μs

^{*2} Design assurance without measurement

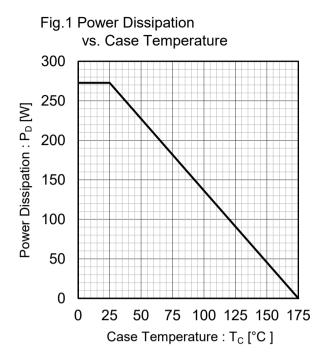
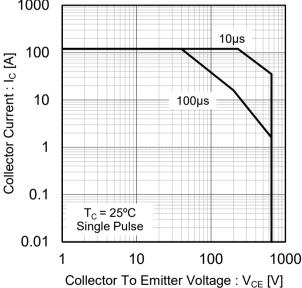


Fig.3 Forward Bias Safe Operating Area

1000



140 120 Collector Current : Ic [A] 100 80 60 40 20 $T_i \le 175^{\circ}C$ V_{GF} = 15V 0 200 400 600 800 Collector To Emitter Voltage: V_{CE} [V]

Fig.4 Reverse Bias Safe Operating Area

Fig.5 Typical Output Characteristics

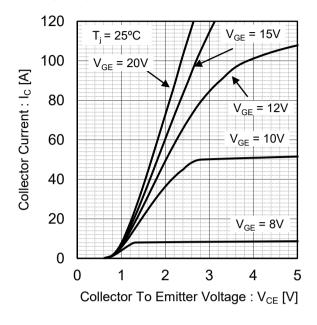


Fig.6 Typical Output Characteristics

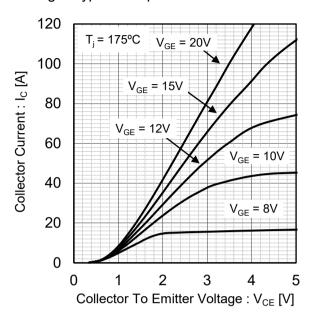


Fig.7 Typical Transfer Characteristics

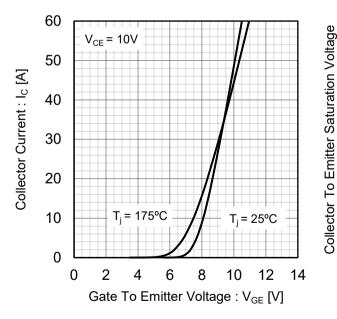
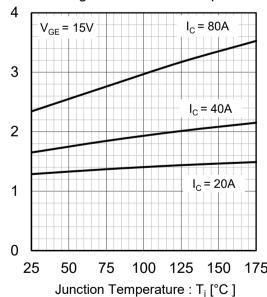


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



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 $: V_{CE(sat)}[V]$

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage 20 Collector To Emitter Saturation Voltage

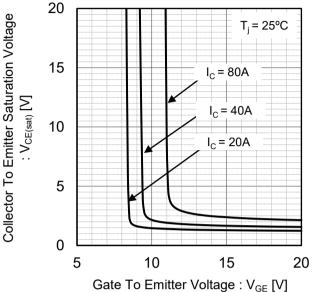


Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

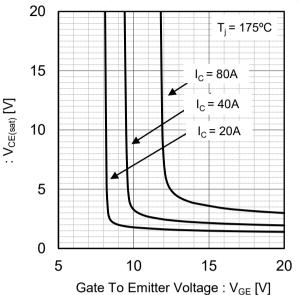


Fig.11 Typical Switching Time vs. Collector Current 1000 Switching Time [ns] 100 $t_{d(off)}$ $t_{d(on)}$ 10 V_{CC} = 400V, V_{GE} = 15V, R_{G} = 10 Ω , T_{j} = 175°C Inductive load 1 0 10 20 30 40 50 60 70 Collecter Current : I_C [A]

Fig.12 Typical Switching Time vs. Gate Resistance 1000 Switching Time [ns] 100 $t_{d(off)}$ $t_{d(on)}$ 10 V_{CC} = 400V, I_C = 40A, V_{GE} = 15V, T_j = 175°C Inductive load 1 0 10 20 30 40 50 Gate Resistance : $R_G [\Omega]$

Collector Current : I_C [A]

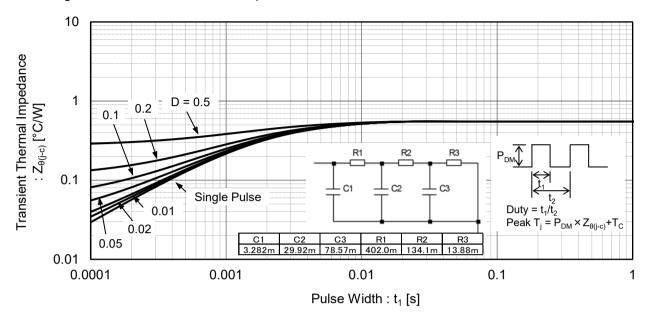
Fig.14 Typical Switching Energy Losses vs. Gate Resistance 10 Switching Energy Losses [mJ] E_{on} 1 E_{off} 0.1 V_{CC} = 400V, I_{C} = 40A, V_{GE} = 15V, T_{j} = 175°C Inductive load 0.01 0 10 20 30 40 50 Gate Resistance : $R_G[\Omega]$

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 C_{ies} 1000 Capacitance [pF] C_oes 100 10 $\mathsf{C}_{\mathsf{res}}$ f = 1MHz $V_{GE} = 0V$ $T_i = 25^{\circ}C$ 1 0.01 0.1 10 100 Collector To Emitter Voltage: V_{CE} [V]

15 V_{CE} = 200V Gate To Emitter Voltage: VGE [V] $V_{CE} = 300V$ 10 V_{CE} = 400V 5 $I_C = 40A$ T_i = 25°C 0 0 10 20 30 40 50 Gate Charge : Qq [nQ]

Fig.16 Typical Gate Charge

Fig.17 IGBT Transient Thermal Impedance



●Inductive Load Switching Circuit and Waveform

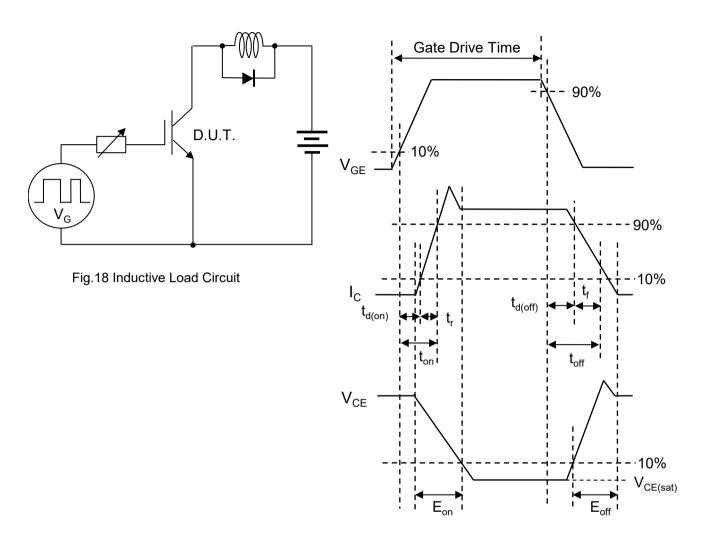


Fig.19 Inductive Load Waveform

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